High-voltage engineering

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Abstract

High-voltage engineering covers the application, the useful use and proper working of high voltages and high fields. Here we give some introductory examples, i.e., 'septa' and 'kicker' at the Large Hadron Collider (14 TeV), the Super Proton Synchrotron (450 GeV) and the Proton Synchrotron (26 GeV) accelerators as found at the European Orginization for Nuclear Research (CERN) today.

We briefly cover the theoretical foundation (Maxwell equations) and aspects of numerical field simulation methods. Concepts relating to electrical fields, insulation geometry and medium and breakdown are introduced. We discuss ways of generating high voltages with examples of AC sources (50/60 Hz), DC sources, and pulse sources.

Insulation and breakdown in gases, liquids, solids and vacuum are presented, including Paschen's law (breakdown field and streamer breakdown). Applications of the above are discussed, in particular the general application of a transformer.

We briefly discuss measurement techniques of partial discharges and loss angle $tan(\delta)$.

The many basic high-voltage engineering technology aspects — high-voltage generation, field calculations, and discharge phenomena — are shown in practical accelerator environments: vacuum feed through (triple points), break-down field strength in air 10 kV/cm, and challenging calculations for real practical geometries.

Exceptionally, the series editor decided that this contribution could be published in the form of a reproduction of the author's transparencies.

High Voltage Engineering

Many thanks to the Electrical Power Systems Group, Eindhoven University of Technology, The Netherlands & CERN AB-BT Group colleagues

Introductory examples

Theoretical foundation and numerical field simulation methods

Generation of high voltages

Insulation and Breakdown

Measurement techniques

CAS on Small Accelerators

Introduction E.Gaxiola:

Studied Power Engineering Ph.D. on Dielectric Breakdown in Insulating Gases; Non-Uniform Fields and Space Charge Effects Industry R&D on Plasma Physics / Gas Discharges CERN Accelerators & Beam, Beam Transfer, Kicker Innovations:

- Electromagnetism
- Beam impedance reduction
- Vacuum high voltage breakdown in traveling wave structures.
- Pulsed power semiconductor applications

CERN Septa and Kicker examples



- Large Hadron Collider 14 TeV
- Super Proton Synchrotron 450 GeV
- Proton Synchrotron 26 GeV

Septum: $E \le 12 \text{ MV/m}$ T = d.c.l = 0.8 - 15 m

- Kicker: V=80kV
 - B = 0.1-0.3 T T = 10 ns 200µs

RF cavities: High gradients, $E \le 150 MV/m$













Generation of High Voltages

• AC Sources (50/60 Hz)

High voltage transformer Resonance source (one coil; divided coils; cascade) (series; parallel)

• DC Sources

Rectifier circuits Electrostatic generator (single stage; cascade) (van de Graaff generator)

Pulse sources

Pulse circuits (single stage; cascade; pulse transformer) Traveling wave generators (PFL; PFN; transmission line transformer)















In Gases

Insulation and Breakdown

Ionisation and Avalanche Formation Townsend and Streamer Breakdown Paschen Law: Gas Type Breakdown Along Insulator Inhomogeneous Fields, Pulsed Voltages, Corona

Insulating Liquids



Breakdown types, Surface tracking, Partial discharges, Polarisation, tan δ

Vacuum Insulation

Applications, Breakdown, Cathode Triple-Point, Insulator Surface Charging, Conditioning





• Electro-negative gasses

Attachment η of electrons to ions electrons: $n_e(x=d) = n_0 e^{(\alpha - \eta)d}$ negative ions: $n_-(x=d) = \frac{n_0 \eta}{\alpha - \eta} [e^{(\alpha - \eta)d} - 1]$

Avalanche ≠ Breakdown; creation of secondaries

Townsend's 2nd ionisation coefficient γ one ion or photon creates γ new electrons at cathode $n_e = \gamma n_0(e^{\alpha d}-1)$

Breakdown if: # secondary electrons $\ge n_0$ $\alpha d \ge \ln(1/\gamma + 1)$









Streamer breakdown

Space charge field $E_{\rho} \approx E_{0}$ • Field enhancement extra ionising collisions (α [↑]) • High excitation \Rightarrow UV photons <u>when</u> 1 electron grows into ca. 10⁸ <u>then</u> E_{ρ} large enough for streamer breakdown ($n_{e} \approx 2 \cdot 10^{8}$ in avalanche head)

Result:

- Secondary avalanches, directional effect (channel formation)
- Grows out into a breakdown within 1 gap crossing (anode and/or cathode directed)

Characteristic:

- Very fast
- Independent of electrodes (no need for electrode surface secondaries)
- Important at large distances (lightning)











Solid insulation

Breakdown field strength:

- Very clean (lab): high
- Practical: lower due to imperfections
 - Voids
 - Absorbed water
 - Contaminations
 - Structural deformations

Anorganic Natural Synthetic	Quartz,mica,glas Porcelain Al ₂ O ₃	Disc insulator Feedthrough Spacer
Paper + Oil		Cable Capacitor
Synthetic Organic Polymerisation	Polyethelene HD,LD,XL – PE Teflon Polystyrene, PVC, polypropene,etc	Spec. properties: Moisture content high T losses bonding
Ероху	Hardener Filler	Moulding in mold

Requirements:

- Mechanical strength
- Contact with electrodes and semiconducting layers
- Resistant to high T, UV, dirt, contamination, rain, ice, desert sand

Problems:

- Surface tracking
 - Partial discharges – In voids (in material or at electrodes,

often created at production).

Types of solid insulation materials





Vacuum insulation

Applications:

- Vacuum circuit breaker
- Cathode Ray Tubes / accelerators
- Elektron microscope
- X-ray tube
- Transceiver tube

What is vacuum?

- "Pressure at which no collisions for Brownian "temperature" movements of electrons"
- $\lambda >>$ characteristic distances
- E.g. $p = 10^{-6}$ bar, $\lambda = 400$ m

- No dielectric losses
 High breakdown fieldstrength
- Non flammable

Advantages: • "Self healing"

• Non toxic, non contaminating

Disadvantages:

- Requires hermetic containment and mechanical support
- Quality determind by:
 - electrodes and insulators
 - Material choice, machining
 - Contaminations, conditioning



Characteristics of vacuum breakdown

No 1st electron from "gas"

Cathode emission

- primary: photoemission, thermic emission, field emission, Schottkyemission
- secondary: e.g. e⁻ bombarded anode \rightarrow ⁺ion collides at cathode \rightarrow e⁻

No breakdown medium

- No multiplication through collision ionisation
- Medium in which the breakdown occurs has to be created ("evaporated" from electrodes, insulators)

Important: prevent field emission

- Keep field at cathode and "cathode triple point" as low as possible
- Insulator surface charging, conditioning



HIGH-VOLTAGE ENGINEERING



- Applications:
- Transformers
- Cables
- Capacitors
- Bushings

Insulating liquids

Requirements:

- Pure, dry and free of gases
- ε_r (high for C's, low for trafo) (demi water $\varepsilon_{r,d,c} = 80$)
- Stable (T), non-flammable, non toxic (pcb's), ageing, viscosity



- No interface problems
- Combined cooling/insulation
- "Cheap" (no mould)
- Liquid tight housing



- Breakdown fieldstrength:
- Very clean (lab): high 1 4 MV/cm (In practice much lower)
- Important at production:outgassing, filtering, drying
- Mineral oil ("old" time application, cheap, flammable)
- Synthetic oil (purer, specifically made, more expensive)
 Silicon oil (very stable up to high T, non-toxic, expensive)
- Liquid H2, N2, Ar, He (supra-conductors)
- **Demi-water** (incidental applications, pulsed power)
- Limitation V_{bd}:
 - Inclusions: Partial discharges \rightarrow Oil decomposition \rightarrow Breakdown
 - Growth (pressure increase)
 - "extension" in field direction"
- **Particles drift** to region with highest $E \rightarrow$ bridge formation \rightarrow breakdown



Transformer:

- Mineral oil: Insulation and cooling
- **Paper**: Barrier for charge carriers and chain formation – Mechanical strength

• Ageing

- Thermical and electrical (partial discharges)
- Lifetime: 30 years, strongly dependent on temperature, short-circuits, overloading, over-voltages
- Breakage of oil moleculs, Creation of gasses, Concentration of various gas components indication for exceeded temperature (as specified in IEC599)

• Lifetime

- Time in which paper looses 50 % of its mechanical strenght
- Strongly dependent on:
 - Moisture (from 0.2 % to 2 % accelerated ageing factor 20)
 - Oxygen (presence accelerates ageing by a factor 2)











Summary

Seen many basic high voltage engineering technology

aspects here:

- High voltage generation
- Field calculations
- Discharge phenomena

The above to be applied in your practical accelerator environments as needed:

- Vacuum feed through: Triple points
- Breakdown field strength in air 10kV/cm
- Challenging calculations for real practical geometries.

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Appendix III Finite Element Method (FEM) Field energy minimal inside each closed region G: $W = \int \frac{1}{2}\varepsilon \left| \vec{E} \right|^2 dV = \int \frac{1}{2}\varepsilon \left| \nabla U \right|^2 dV$ Assume U satisfies Laplace equation, but U' does <u>not</u>, then $W_{U'} - W_U \ge 0:$ $W_{U'} - W_U = \frac{1}{2}\varepsilon \iiint (|\nabla U'|^2 - |\nabla U|^2) dV = \dots = \frac{1}{2}\varepsilon \iiint |\nabla U' - \nabla U|^2 dV \ge 0$ Field energy for one element (2-dim) Potential is linear inside element: $U = a + bx + cy = (1 - x - y) \begin{pmatrix} a \\ b \\ c \end{pmatrix}$ $\int \frac{1}{2} \left(\sum_{l=1}^{l} \sum_{\substack{i=1, x - y_l \\ i=x - y_l} \sum_{\substack{i=1, x - y_l \\ i=$





Appendix II Electrical Fields

Vacuum and matter

Dielectric displacement **D** Magnetic induction **B** Ohm's law: relation between current density **J** in a conductor and specific conduction σ_s (=1/ ρ_s) and electrical field **E** $\vec{D} = \varepsilon_0 \vec{E} + \vec{P} = \varepsilon_0 \varepsilon_r \vec{E} = \varepsilon \vec{E}$; $\vec{B} = \mu_0 (\vec{H} + \vec{M}) = \mu_0 \mu_r \vec{H} = \mu \vec{H}$; $\vec{J} = \sigma_s \vec{E}$ (9,10,11) Polarisation **P** Magnetisation **M**

(Static) boundary conditions for normal (index n) and tangential (index t) field components in terms of surface charge and surface current:

$$\oint D \cdot dA = Q_{omsl.} \qquad \Rightarrow \qquad D_{1n} - D_{2n} = \sigma \qquad (12)$$

$$\oint E \cdot dl = 0 \qquad \Rightarrow \qquad E_{1t} - E_{2t} = 0 \tag{13}$$

$$\oint B \cdot dA = 0 \qquad \implies \qquad B_{1n} - B_{2n} = 0 \tag{14}$$

$$\oint \vec{H} \cdot \vec{dl} = I_{omsl.} \qquad \Rightarrow \qquad H_{1t} - H_{2t} = J^*$$
(15)

Conservation of charge / continuity of current

Ampere's law (8) in differential form gives:

$$\vec{\nabla} \cdot \left(\vec{\nabla} \times \vec{H}\right) = \vec{\nabla} \cdot \left(\vec{J} + \frac{\partial \vec{D}}{\partial t}\right) = 0 \qquad \Rightarrow \qquad \vec{\nabla} \cdot \vec{J} + \frac{\partial \rho}{\partial t} = 0 \tag{16}$$

Gauss Theorem gives the integral form:

$$\oint (\vec{J} + \frac{\partial D}{\partial t}) \cdot \vec{dA} = 0 \quad \text{or} \qquad \oint \vec{J} \cdot \vec{dA} + \frac{\partial Q_{omsl.}}{\partial t} = 0 \tag{17}$$

Electrical potential

(6) Gradient or (scalar) potential U:

$$\vec{\nabla} \times \vec{E} = \vec{0}$$
 define $\vec{E} = -\vec{\nabla}U \implies U(x) = -\int_{x'(U=0)}^{x} \vec{E} \cdot \vec{dl}$ (21)

$$\vec{\nabla} \cdot \vec{E} = -\vec{\nabla} \cdot \vec{\nabla} U = -\Delta U$$
 so $\Delta U = -\frac{\rho}{\varepsilon}$ (Poisson) (22)

Without space charge:
$$\Delta U = 0$$
 (Laplace) (23)

Equations define every position in space between potential and charge distribution, given the boundary conditions.

Definition of potential only valid in the absence of varying magnetic induction. If $\partial B/\partial t \neq 0$ no more (scalar) potentials, only voltage differences, which have become dependent on the path (non-conservative field):

$$\sum_{C_1} \vec{E} \cdot \vec{dl} - \int_{C_2} \vec{E} \cdot \vec{dl} = \oint \vec{E} \cdot \vec{dl} = -\frac{d}{dt} \iint \vec{B} \cdot \vec{dA}$$
(24)

or

$$[V_1 - V_2]_{via C_1} - [V_1 - V_2]_{via C_2} \neq 0$$
(25)



с²

C,

x ₁

Gauss' law in integral form (1), charges \rightarrow E-field (and potential) for configuration. Potential equations (22) or (23) for given boundary conditions \rightarrow potential and E-field.

Fields from charges			Fields from Potentials		
\Rightarrow	Е	Laplace / Poisson + boundary	$(V) \Rightarrow$	U	
\Rightarrow	U	Differentiation of U	\Rightarrow	E	
\Rightarrow	V	E and Gauss' law	\Rightarrow	Q	
\Rightarrow	С	Q and V	\Rightarrow	С	
	$\begin{array}{c} \text{arges} \\ \Rightarrow \\ \Rightarrow \\ \Rightarrow \\ \Rightarrow \\ \Rightarrow \end{array}$	arges \Rightarrow E \Rightarrow U \Rightarrow V \Rightarrow C	argesFields from Potential \Rightarrow ELaplace / Poisson + boundary \Rightarrow UDifferentiation of U \Rightarrow VE and Gauss' law \Rightarrow CQ and V	argesFields from Potentials \Rightarrow ELaplace / Poisson + boundary (V) \Rightarrow \Rightarrow UDifferentiation of U \Rightarrow VE and Gauss' law \Rightarrow CQ and V	

Fields from charges

Gauss' law, electrical field coupled to charge. Two concentric spheres:



$$\oint \varepsilon_0 \varepsilon_r \vec{E} \cdot \vec{dA} = Q \quad \Rightarrow \quad E = \frac{Q}{4\pi\varepsilon_o \varepsilon_r r^2}$$
(26)

$$U(r) = -\int E(r) dr = \frac{Q}{4\pi\varepsilon_0\varepsilon_r r} + Integration constant$$
(27)

Potential in infinity zero \rightarrow

$$U(r) = \frac{Q}{4\pi\varepsilon_0\varepsilon_r r}$$

Capacity of sphere with radius r₀:

$$C = \frac{Q}{U(r_0)} = \frac{Q}{V} = 4\pi\varepsilon_0\varepsilon_r r_0$$
⁽²⁹⁾

Field maximum on sphere surface:

$$E_{\max} = E(r_0) = \frac{Q}{4\pi\varepsilon_0\varepsilon_r r_0^2} = \frac{V}{r_0}$$
(30)

Concentric metal spheres



$$U(r) = \frac{Q}{4\pi\varepsilon_0\varepsilon_r} \left[\frac{r_2 - r}{r_2 r} \right] \quad (r_1 \le r \le r_2)$$
(31)

$$C = 4\pi\varepsilon_0\varepsilon_r \frac{r_1 r_2}{r_2 - r_1}$$
(32)

Maximum field on surface inner sphere:

$$E_{\max} = E(r_1) = \frac{V}{r_1(1 - r_1/r_2)}$$
(33)

Concentric cylinders

Two concentric cylinders with inner radius r₁ and outer radius r₂:

$$E(r) = \frac{Q/l}{2\pi\varepsilon_0\varepsilon_r r} \implies U(r) = \frac{Q/l}{2\pi\varepsilon_0\varepsilon_r} \cdot \ln(r_2/r)$$
(34)

$$C_{l} = \frac{2\pi\varepsilon_{0}\varepsilon_{r}}{\ln(r_{2}/r_{1})}$$
(35)

$$E_{\max} = \frac{V}{r_1 \ln(r_2 / r_1)}$$
(36)

Fields from potential equations

Poisson equation or (without space charge, $\rho = 0$) Laplace:

Poisson:
$$\Delta U = -\frac{\rho}{\varepsilon}$$
 (37)
Laplace: $\Delta U = 0$

General solution + boundary conditions \rightarrow specific solution.

Differentiation gives E-field, applying Gauss gives the charge. From charge and voltage \rightarrow capacity.

Laplace equation in Cartesian, cylindrical or spherical coordinates:

Carthesian:
$$\frac{\partial^{2}U}{\partial x^{2}} + \frac{\partial^{2}U}{\partial y^{2}} + \frac{\partial^{2}U}{\partial z^{2}} = 0$$
Cylindrical:
$$\frac{1}{r}\frac{\partial}{\partial r}\left[r\frac{\partial U}{\partial r}\right] + \frac{1}{r^{2}}\frac{\partial^{2}U}{\partial \vartheta^{2}} + \frac{\partial^{2}U}{\partial z^{2}} = 0$$
(38)
Sphere:
$$\frac{1}{r^{2}}\frac{\partial}{\partial r}\left[r^{2}\frac{\partial U}{\partial r}\right] + \frac{1}{r^{2}\sin\vartheta}\frac{\partial}{\partial\vartheta}\left[\sin\vartheta\frac{\partial U}{\partial\vartheta}\right] + \frac{1}{r^{2}\sin\vartheta}\frac{\partial^{2}U}{\partial\varphi^{2}} = 0$$

Concentric spheres

Two concentric metal spheres. Only r-dependent (38):

$$\frac{1}{r^{2}}\frac{\partial}{\partial r}\left[r^{2}\frac{\partial U}{\partial r}\right] = 0 \implies \frac{\partial U}{\partial r} = \frac{C_{1}}{r^{2}} \implies U = -\frac{C_{1}}{r} + C_{2}$$
and
$$E = -\frac{C_{1}}{r^{2}}$$
(45)

→ Result: spherical equipotential surfaces. With boundary conditions on inner sphere $U(r_1) = V$ and on outer sphere $U(r_2) = 0$:

$$U = \frac{r_1}{r} \left(\frac{r_2 - r}{r_2 - r_1} \right) V \text{ and } E = \left(\frac{r_1 r_2}{r_2 - r_1} \right) \frac{V}{r^2}$$
(46)

Charge on the sphere Q and C = Q/V:

$$Q = \oiint \varepsilon_0 \varepsilon_r \vec{E} \cdot \vec{dA} = 4\pi \varepsilon_0 \varepsilon_r \left(\frac{r_1 r_2}{r_2 - r_1}\right) V \quad and \quad C = 4\pi \varepsilon_0 \varepsilon_r \left(\frac{r_1 r_2}{r_2 - r_1}\right)$$
(47)

Cylinder in a uniform field



$$U = -E_0 r \cos \vartheta = -E_0 x \tag{48}$$

$$U(r) = -E_0 r \cos \vartheta + \sum_{m=1}^{\infty} d_m r^{-m} \left(g_m \cos(m \vartheta) + h_m \sin(m \vartheta) \right)$$
(49)

$$U(r,\vartheta) = -E_0 \left(r - \frac{a^2}{r}\right) \cos \vartheta \tag{50}$$

$$E_r = -\frac{\partial U}{\partial r} = E_0 \left(1 + \frac{a^2}{r^2} \right) \cos \vartheta \quad and \quad E_\vartheta = -\frac{1}{r} \frac{\partial U}{\partial \vartheta} = -E_0 \left(1 - \frac{a^2}{r^2} \right) \sin \vartheta$$
(51)

Maximum field $2 \cdot E_0$ at $(r, \theta) = (a, 0)$ and the tangential field is zero on r = a.

Fields from transformations

Graphical method

The graphical method uses properties as described more extensively in Alston [4]. Example:

- 1. Draw E-lines and U-lines in uniform area.
- 2. Divide U in equal partitions
- 3. Choose a "mesh factor".
- 4. Draw the "guessed" U-lines in the non-uniform area, which fit continuously to those in the uniform area.
- 5. Now draw the E-lines such that the mesh factor is respected.
- 6. Correct where necessary the U-lines, repeat the procedure with the E-lines, and refine if needed.



For areas with different dielectrics ε_r , the mesh factor changes (see example above). Since the field lines are drawn on equal flux distances $\delta \psi$ we in fact draw D-lines.

On an interface between dielectrics we in addition get dielectric refraction.

On the interface E_t and D_n are continuous \rightarrow



The field becomes non-uniform, with field enhancement at point P.



Conformal mapping

Conformal mapping is a mathematical method to determine E-fields in two dimensional, z-independent cases (see Binns [5] or Feynman [6]). We consider a complex analytical function f(z) of the complex variable z; i.e. a function for which in an area both f(z) and its derivative f'(z) exist. Complex function theory shows the transformation defined by f(z) to be conform, except for those points where the derivative f'(z) equals zero (see e.g. Kreyszig [7]). Conformal mapping assumes the transformed angles to be "conform". We will use this property to transform a E-U field to a different pattern which again we can interpret as a E-U plot.



Hulpvlak

A mathematical help surface, the w-surface with coordinates u and v, is projected onto the "technical" z-surface, with coordinates x and y, for which we want to obtain a field. Consider the coordinates: z = x + iy and w = f(z) = u + iy, with x and y on the technical surface

and u and v on the mathematical surface.

For a function f(z) with which the z-surface is projected onto the w-surface we can show:

$$f'(z) = \frac{\lim_{\Delta z \to 0} \frac{f(z + \Delta z) - f(z)}{\Delta z}}{\Delta z} \implies f'(z) = \frac{\partial u}{\partial x} + j\frac{\partial v}{\partial x} \quad and \quad f'(z) = -j\frac{\partial u}{\partial y} + \frac{\partial v}{\partial y} \quad (59)$$

The first for $\Delta z \rightarrow 0$ for $\Delta y=0$ and $\Delta x \rightarrow 0$. The second for $\Delta x=0$ and $\Delta y \rightarrow 0$. Both derivatives are equal for an analytical function:

$$\frac{\partial u}{\partial x} = \frac{\partial v}{\partial y}$$
 en $\frac{\partial u}{\partial y} = -\frac{\partial v}{\partial x}$ (60)

The so called Cauchy-Riemann equations.

It can be shown, for all functions that satisfy these criteria to be analytical. Both the function u(x,y) as well as v(x,y) fulfill the Laplace equation, as can be seen when applying Cauchy-Riemann:

$$\Delta u = \frac{\partial^2 u}{\partial x^2} + \frac{\partial^2 u}{\partial y^2} = \frac{\partial^2 v}{\partial x \partial y} - \frac{\partial^2 v}{\partial y \partial x} = 0 \quad ; \qquad \Delta v = \frac{\partial^2 v}{\partial x^2} + \frac{\partial^2 v}{\partial y^2} = -\frac{\partial^2 u}{\partial x \partial y} + \frac{\partial^2 u}{\partial y \partial x} = 0 \tag{61}$$

We can interpret u as potential and v as field or vice versa. We now choose in the w-surface the simplest field projection meeting the Laplace requirement, e.g. equipotential lines u = cst and Elines v = cst. Every transformation of the z-surface gives a projection meeting Laplace's equation, and which we can interpret as field projection. The projection of u = cst is again to be interpreted as equipotential line, and the projection of v = cst as E-line, or vice versa.

The generated field projection only depends on the transformation function w = f(z). See Binns [5] or Bewley [8] for a more systematical method for determining such functions, the so called Schwartz-Christoffel transformation method.



Shown here is an example for the function $w = f(z) = z^2$.

 $u + jv = (x + jy)^{2} = x^{2} - y^{2} + 2jxy$ (62)

Transformation of u = cst and v = cst gives the contours:

 $u = x^2 - y^2 = cst$ and v = xy = cst (63)

These are hyperboles crossing each other under a 90° angle.

To be interpreted as two electrodes in one quadrant, under an angle of 90° : x- and y-axes together form one electrode (projection of v = 0), the other electrode is the projection of any other line with v = constant.